

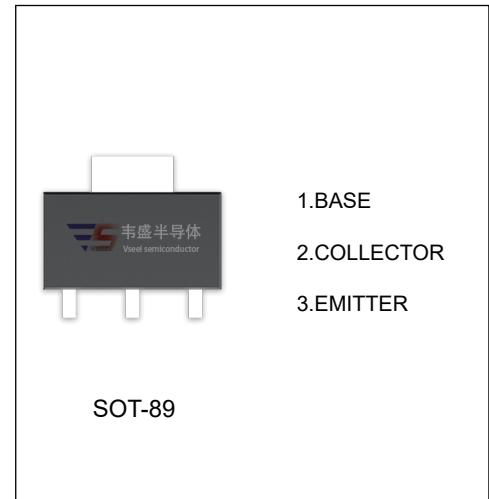
2SA1662 TRANSISTOR (PNP)

FEATURES

Complementary to KTC4374

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	-80	V
V _{CEO}	Collector-Emitter Voltage	-80	V
V _{EBO}	Emitter-Base Voltage	-5	V
I _C	Collector Current -Continuous	-0.4	A
P _C	Collector Power Dissipation	0.5	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-1mA, I _E =0	-80			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-10mA, I _B =0	-80			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-1mA, I _C =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-80V, I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-5V, I _C =0			-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-2V, I _C =-50mA	70		240	
	h _{FE(2)}	V _{CE} =-2V, I _C =-200mA	40			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-200mA, I _B =-20mA			-0.4	V
Base-emitter voltage	V _{BE}	V _{CE} =-2V, I _C =-5mA	-0.55		-0.8	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-10mA		120		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		14		pF

CLASSIFICATION OF h_{FE(1)}

Rank	O	Y
Range	70-140	120-240
Marking	FO	FY